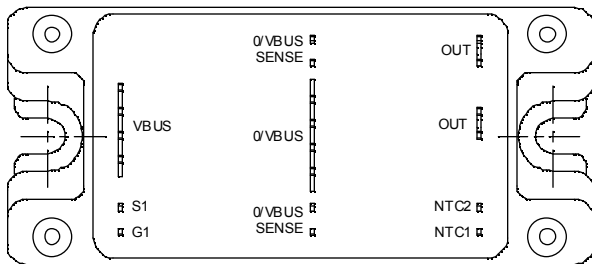
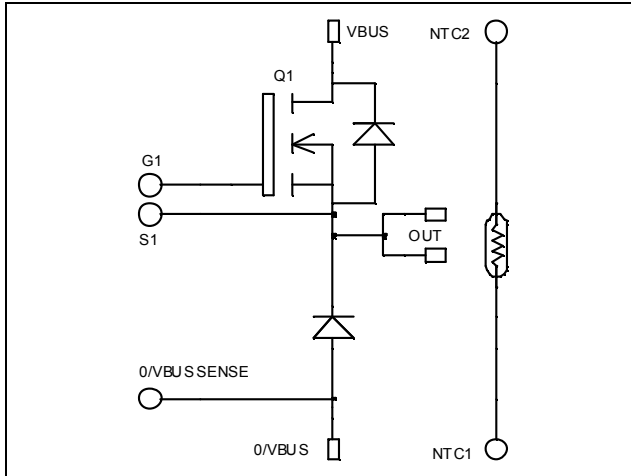


Buck chopper MOSFET Power Module

$V_{DSS} = 500V$

$R_{DSon} = 38m\Omega$ typ @ $T_j = 25^\circ C$

$I_D = 90A$ @ $T_c = 25^\circ C$



Application

- AC and DC motor control
- Switched Mode Power Supplies

Features

- Power MOS 7[®] MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	500	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	A
		$T_c = 80^\circ C$	
I_{DM}	Pulsed Drain current	360	
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	45	m Ω
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	W
I_{AR}	Avalanche current (repetitive and non repetitive)	46	A
E_{AR}	Repetitive Avalanche Energy	50	mJ
E_{AS}	Single Pulse Avalanche Energy	2500	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 500\text{V}$			200	μA
		$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 400\text{V}$			1000	
$R_{\text{DS(on)}}$	Drain – Source on Resistance	$V_{\text{GS}} = 10\text{V}, I_{\text{D}} = 45\text{A}$		38	45	$\text{m}\Omega$
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{\text{GS}} = V_{\text{DS}}, I_{\text{D}} = 5\text{mA}$	3		5	V
I_{GSS}	Gate – Source Leakage Current	$V_{\text{GS}} = \pm 30\text{V}, V_{\text{DS}} = 0\text{V}$			± 150	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{\text{GS}} = 0\text{V}$		11.2		nF
C_{oss}	Output Capacitance	$V_{\text{DS}} = 25\text{V}$		2.4		
C_{rss}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		0.18		
Q_{g}	Total gate Charge	$V_{\text{GS}} = 10\text{V}$		246		nC
Q_{gs}	Gate – Source Charge	$V_{\text{Bus}} = 250\text{V}$		66		
Q_{gd}	Gate – Drain Charge	$I_{\text{D}} = 90\text{A}$		130		
$T_{\text{d(on)}}$	Turn-on Delay Time	Inductive switching @ 125°C $V_{\text{GS}} = 15\text{V}$ $V_{\text{Bus}} = 333\text{V}$ $I_{\text{D}} = 90\text{A}$ $R_{\text{G}} = 2\Omega$		18		ns
T_{r}	Rise Time			35		
$T_{\text{d(off)}}$	Turn-off Delay Time			87		
T_{f}	Fall Time			77		
E_{on}	Turn-on Switching Energy	Inductive switching @ 25°C $V_{\text{GS}} = 15\text{V}, V_{\text{Bus}} = 333\text{V}$ $I_{\text{D}} = 90\text{A}, R_{\text{G}} = 2\Omega$		1510		μJ
E_{off}	Turn-off Switching Energy			1452		
E_{on}	Turn-on Switching Energy	Inductive switching @ 125°C $V_{\text{GS}} = 15\text{V}, V_{\text{Bus}} = 333\text{V}$ $I_{\text{D}} = 90\text{A}, R_{\text{G}} = 2\Omega$		2482		μJ
E_{off}	Turn-off Switching Energy			1692		

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		600			V
I_{RM}	Maximum Reverse Leakage Current	$V_{\text{R}} = 600\text{V}$	$T_j = 25^\circ\text{C}$		250	μA
			$T_j = 125^\circ\text{C}$		500	
I_{F}	DC Forward Current	$T_c = 70^\circ\text{C}$		60		A
V_{F}	Diode Forward Voltage	$I_{\text{F}} = 60\text{A}$		1.6	1.8	V
		$I_{\text{F}} = 120\text{A}$		1.9		
		$I_{\text{F}} = 60\text{A}$	$T_j = 125^\circ\text{C}$	1.4		
t_{rr}	Reverse Recovery Time	$I_{\text{F}} = 60\text{A}$ $V_{\text{R}} = 400\text{V}$ $di/dt = 200\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$	130		ns
			$T_j = 125^\circ\text{C}$	170		
Q_{rr}	Reverse Recovery Charge	$T_j = 25^\circ\text{C}$		220		nC
			$T_j = 125^\circ\text{C}$	920		

Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance	Transistor		0.18	°C/W
		Diode		0.9	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, I _{isol} <1mA, 50/60Hz	2500			V
T _J	Operating junction temperature range	-40		150	°C
T _{STG}	Storage Temperature Range	-40		125	
T _C	Operating Case Temperature	-40		100	
Torque	Mounting torque	To Heatsink	M5	2.5	N.m
Wt	Package Weight			160	g

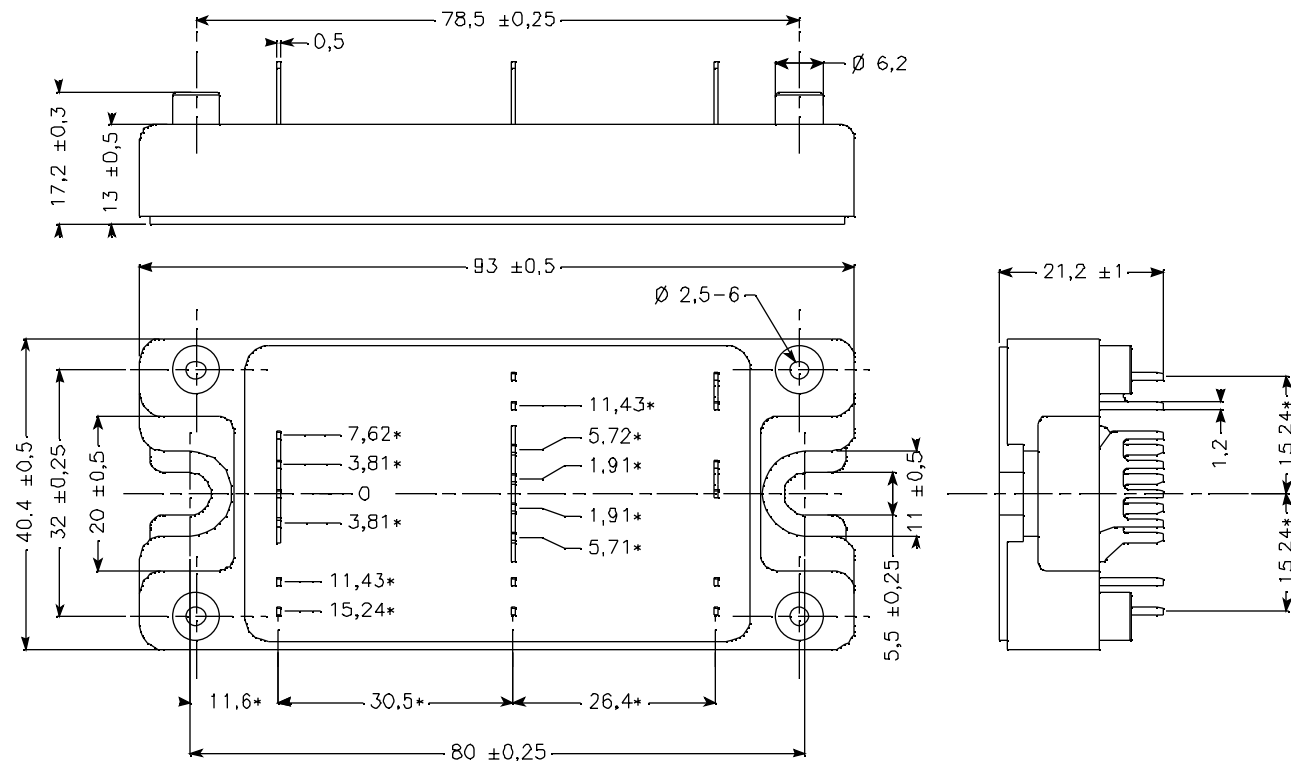
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B _{25/85}	T ₂₅ = 298.15 K		3952		K

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

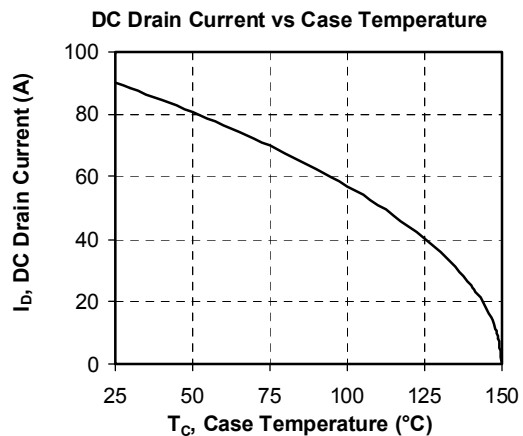
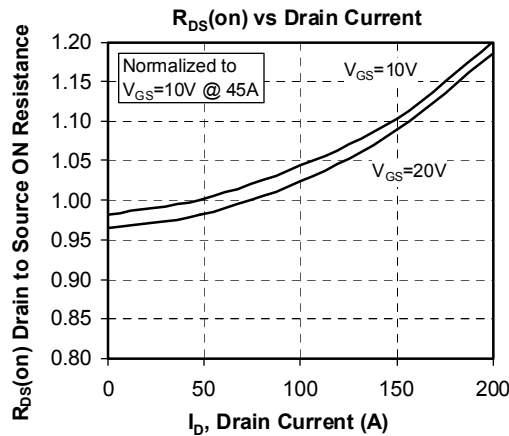
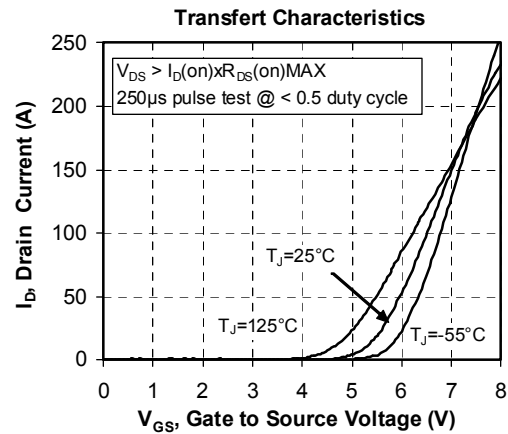
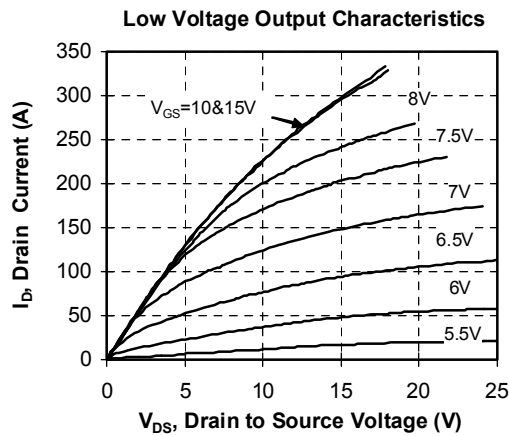
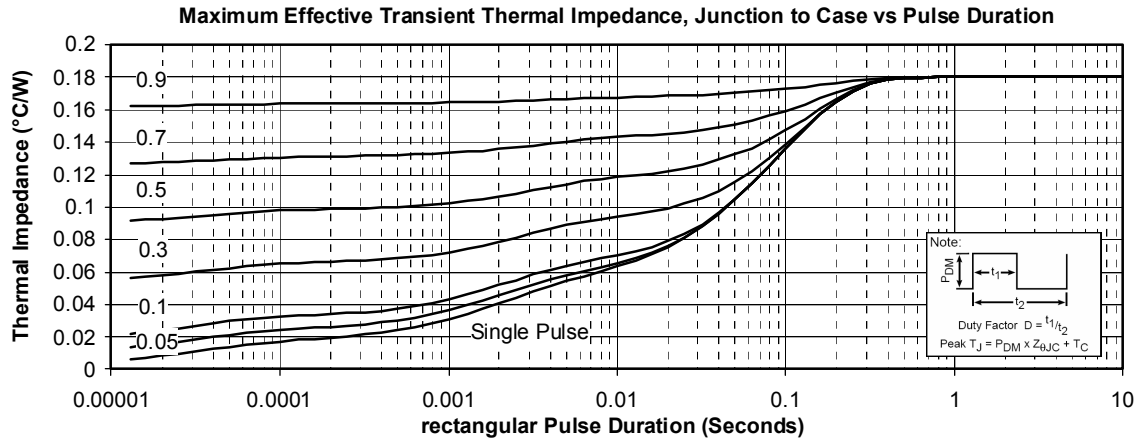
SP4 Package outline (dimensions in mm)

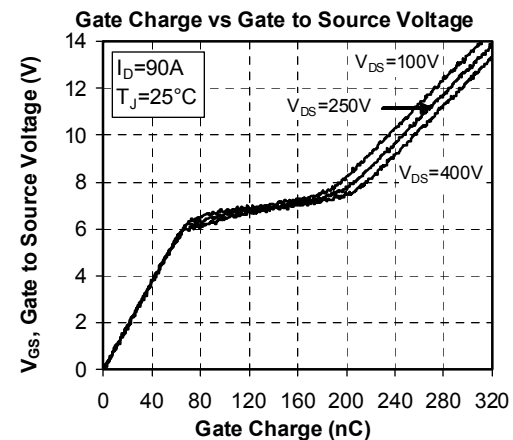
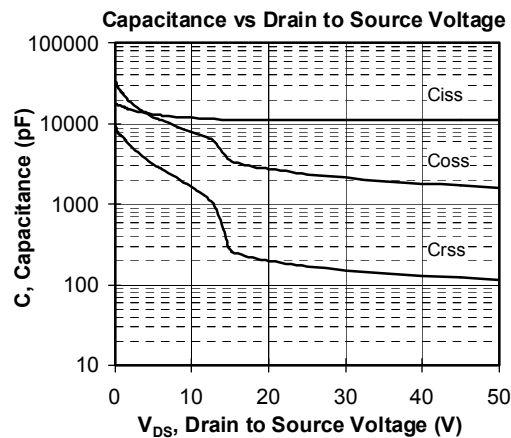
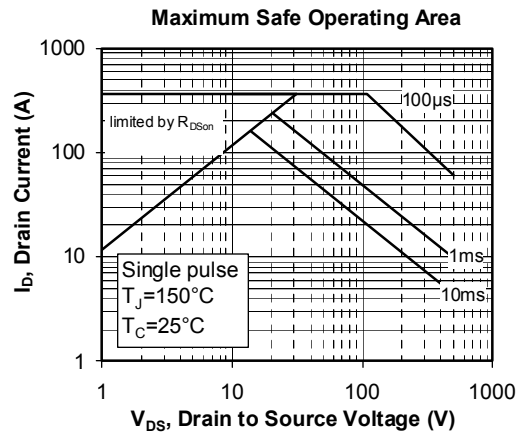
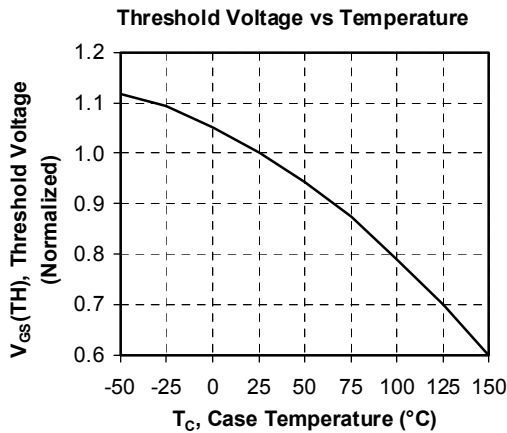
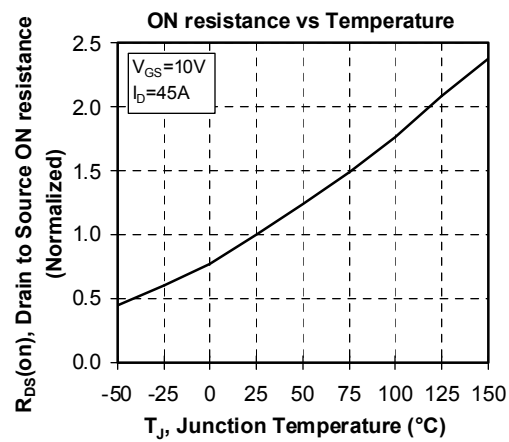
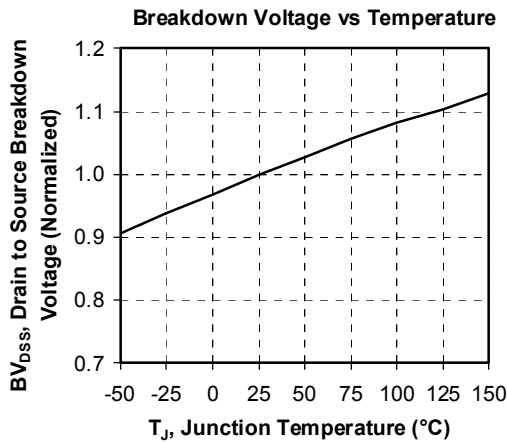


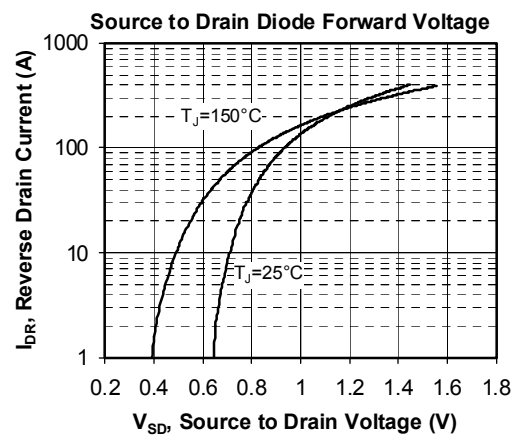
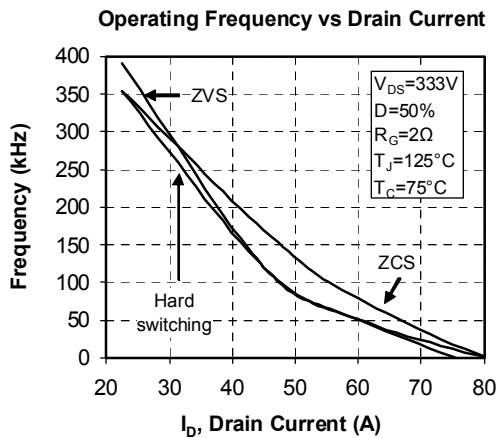
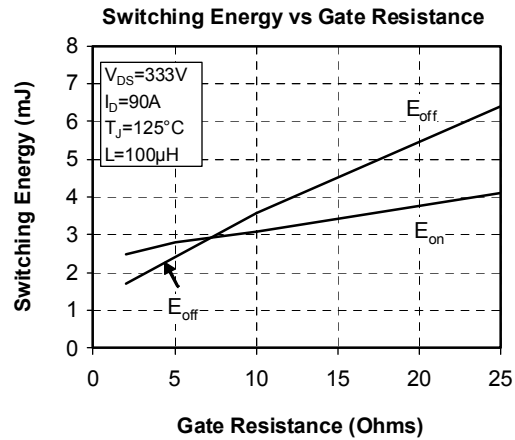
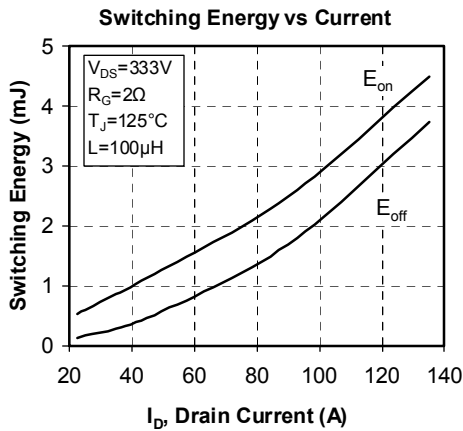
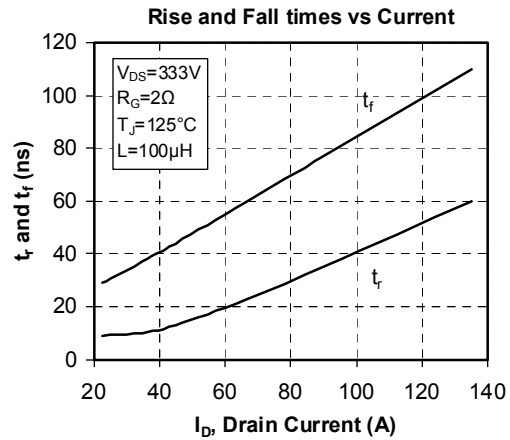
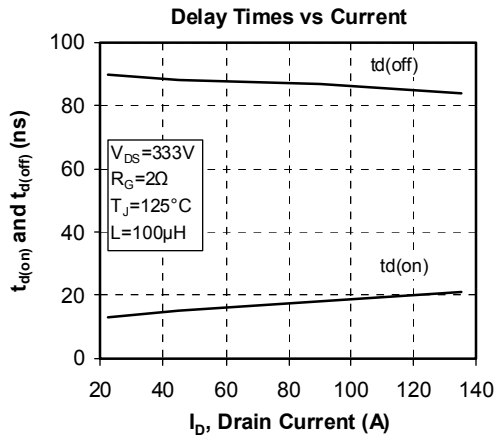
ALL DIMENSIONS MARKED "*" ARE TOLERENCED AS: ± 0.1

See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

Typical Performance Curve







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